

20 V, 0.5 A very low $V_{\rm F}$ MEGA Schottky barrier rectifier in leadless ultra small SOD882 package

Rev. 01 — 11 February 2004

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection encapsulated in a SOD882 leadless ultra small plastic package.

1.2 Features

- Forward current: 0.5 A
- Reverse voltage: 20 V
- Very low forward voltage
- Leadless ultra small plastic package
- Power dissipation comparable to SOT23.

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Low voltage rectification
- High efficiency DC-to-DC conversion
- Low power consumption applications.

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Value	Unit
I _F	forward current	0.5	А
V _R	reverse voltage	20	V



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2. Pinning information

Table 2:	Discrete pinning	
Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 1 2 sym001 Bottom view Top view 001aaa332

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3: Ord	ering infor	nation	
Type number	Package		
	Name	Description	Version
PMEG2005EL	-	leadless ultra small plastic package; 2 terminals; body $1.0 \times 0.6 \times 0.5$ mm	SOD882

4. Marking

Table 4: Marking	
Type number	Marking code
PMEG2005EL	F5

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V _R	continuous reverse voltage		-	20	V
I _F	continuous forward current		-	0.5	А
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	2.5	A
I _{FSM}	non-repetitive peak forward current	t = 8 ms square wave	-	3.0	A
Tj	junction temperature		<u>[1]</u> -	150	°C
T _{amb}	operating ambient temperature		<u>[1]</u> –65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

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[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

6. Thermal characteristics

Table 6:	Thermal characteristics				
Symbol	Parameter	Conditions		Value	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1][2]</u>	500	K/W

[1] Refer to SOD882 standard mounting conditions (footprint), FR4 with 60 µm copper strip line.

[2] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F (AV)} rating will be available on request.

7. Characteristics

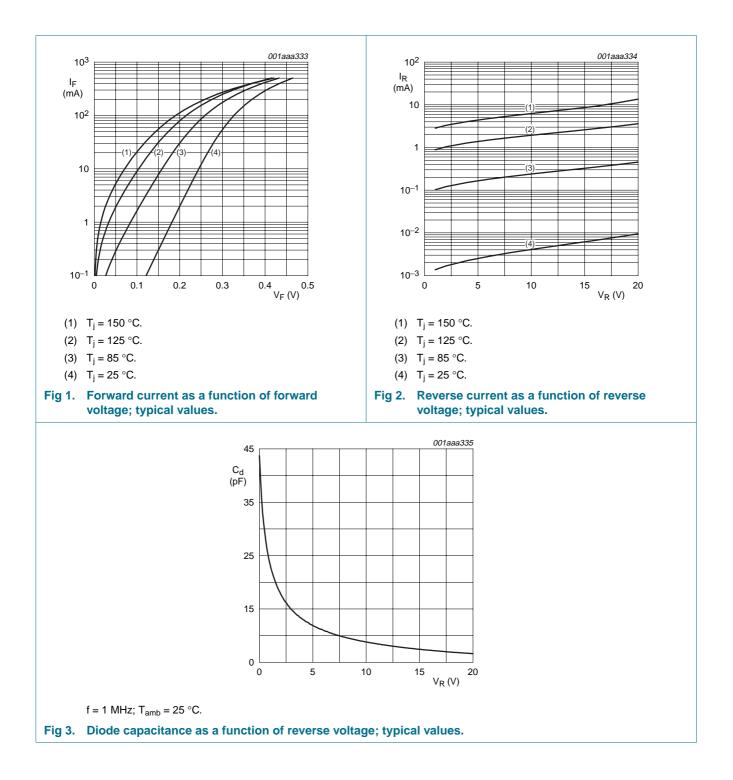
Table 7: Characteristics

T_{amb} = 25 °C unless otherwise specified.

Parameter			_		
	Conditions		Тур	Max	Unit
continuous forward voltage	see <mark>Figure 1</mark> I _F = 0.1 mA		125	180	mV
	I _F = 1 mA		185	240	mV
	I _F = 10 mA		250	290	mV
	I _F = 100 mA		325	380	mV
	I _F = 500 mA		450	500	mV
continuous reverse current	$V_R = 10 V$; see <u>Figure 2</u>	<u>[1]</u>	4	30	μA
diode capacitance	V _R = 1 V; f = 1 MHz; see <u>Figure 3</u>		24	30	pF
	forward voltage continuous reverse current	forward voltage $I_{F} = 0.1 \text{ mA}$ $I_{F} = 1 \text{ mA}$ $I_{F} = 10 \text{ mA}$ $I_{F} = 100 \text{ mA}$ $I_{F} = 500 \text{ mA}$ continuous reverse current diode capacitance $V_{R} = 10 \text{ V}; \text{ see Figure 2}$	forward voltage $I_{F} = 0.1 \text{ mA}$ $I_{F} = 1 \text{ mA}$ $I_{F} = 10 \text{ mA}$ $I_{F} = 10 \text{ mA}$ $I_{F} = 100 \text{ mA}$ $I_{F} = 500 \text{ mA}$ continuous $V_{R} = 10 \text{ V}; \text{ see } \underline{Figure 2}$ I_{I} diode capacitance $V_{R} = 1 \text{ V}; f = 1 \text{ MHz};$	forward voltage $I_F = 0.1 \text{ mA}$ $I_F = 1 \text{ mA}$ $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 500 \text{ mA}$ $V_R = 10 \text{ V}; \text{ see } Figure 2$ $I_1 \text{ for every equation of } V_R = 1 \text{ V}; \text{ f} = 1 \text{ MHz};$ $I_F = 10 \text{ mA}$	

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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8. Package outline

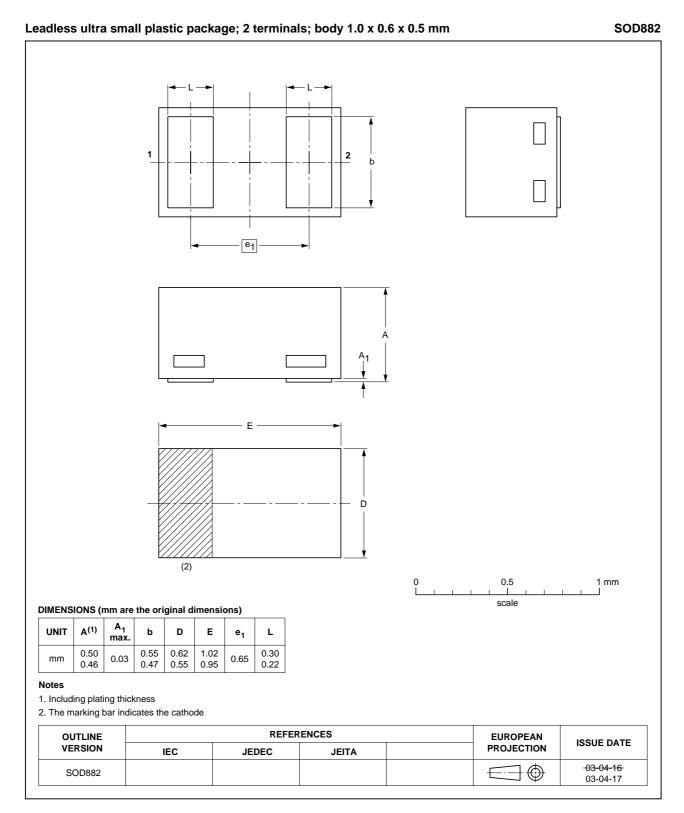


Fig 4. Package outline.

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9. Revision history

Table 8: Revision	history				
Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMEG2005EL_1	20040211	Product specification	-	9397 750 12464	-

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10. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Date of release: 11 February 2004 Document order number: 9397 750 12464

Published in The Netherlands